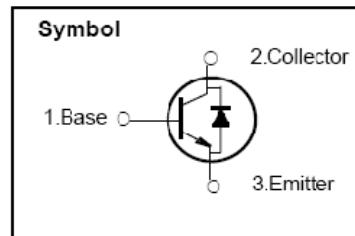


## *High Voltage Fast-Switching NPN Power Transistor*

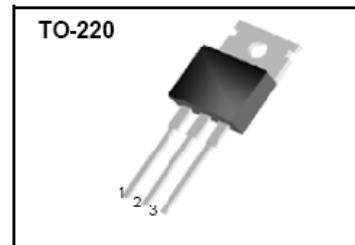
### Features

- ◆ Very High Switching Speed
- ◆ Minimum Lot-to-Lot  $h_{FE}$  Variation
- ◆ Wide Reverse Bias SOA
- ◆ Built-in free wheeling diode



### General Description

This Device is designed for high voltage, High speed switching characteristics required such as lighting system, switching mode power supply.



### Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Units
$V_{CES}$	Collector-Emitter Voltage	$V_{BE} = 0$	700	V
$V_{CEO}$	Collector-Emitter Voltage	$I_B = 0$	400	V
$V_{EBO}$	Emitter-Base Voltage	$I_C = 0$	9.0	V
$I_C$	Collector Current		8.0	A
$I_{CP}$	Collector pulse Current		16	A
$I_B$	Base Current		4.0	A
$I_{BM}$	Base Peak Current	$t_P = 5\text{ms}$	8.0	A
$P_C$	Total Dissipation at $TC = 25^\circ\text{C}$		80	W
$T_J$	Operation Junction Temperature		- 40 ~ 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature		- 40 ~ 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance Junction to Case	1.67	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	62.5	$^\circ\text{C}/\text{W}$

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## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
$I_{CEV}$	Collector Cut-off Current ( $V_{BE} = -1.5\text{V}$ )	$V_{CE} = 700\text{V}$ $V_{CE} = 700\text{V}, T_C = 100^\circ\text{C}$	-	-	1.0 5.0	mA
$V_{CEO(\text{sus})}$	Collector-Emitter Sustaining Voltage	$I_B = 0, IC = 10\text{mA}$	400	-	-	V
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C = 2.0\text{A}, I_B = 0.4\text{A}$ $I_C = 5.0\text{A}, I_B = 1.0\text{A}$ $I_C = 8.0\text{A}, I_B = 2.0\text{A}$	-	-	0.6 1.5 3.0	V
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C = 2.0\text{A}, I_B = 0.4\text{A}$ $I_C = 5.0\text{A}, I_B = 1.0\text{A}$	-	-	1.2 1.6	V
$h_{FE}$	DC Current Gain	$I_C = 2.0\text{A}, V_{CE} = 5\text{V}$ $I_C = 5.0\text{A}, V_{CE} = 5\text{V}$	10 10		40 30	
$t_s$ $t_f$	Storage Time Fall Time	$I_C = 5.0\text{A}, V_{CC} = 125\text{V}$ $I_{B1} = 1.0\text{A}, I_{B2} = -1.0\text{A}$ $T_P = 25\mu\text{s}$	-	-	3.6 1.6	$\mu\text{s}$
$f_T$	Current Gain Bandwidth Product	$I_C = 0.5\text{A}, V_{CE} = 10\text{V}$	4	-	-	MHz
$V_F$	Diode Forward Voltage	$I_F = 2\text{A}$	-	-	2.5	V
$C_{OB}$	Output Capacitance	$I_C = 0.5\text{A}, V_{CE} = 10\text{V}$	-	6.5		pF

### Note:

Pulse Test : Pulse width 300, Duty cycle 2%

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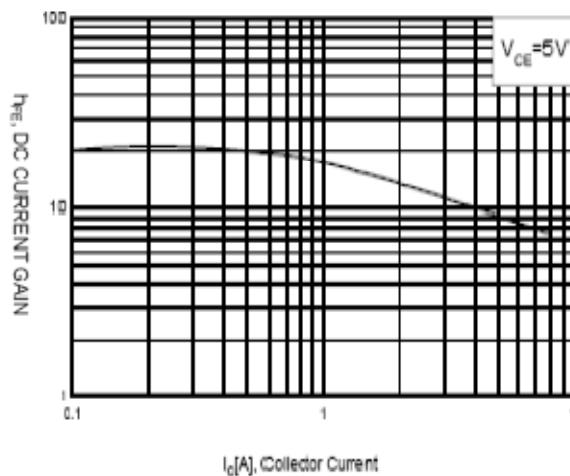


Fig. 1 DC Current Gain

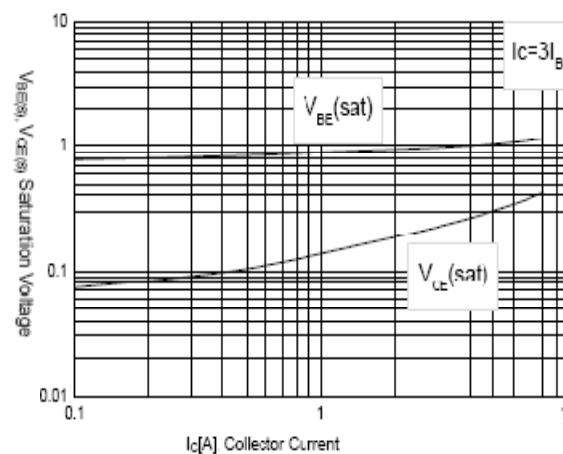


Fig. 2 Saturation Voltage

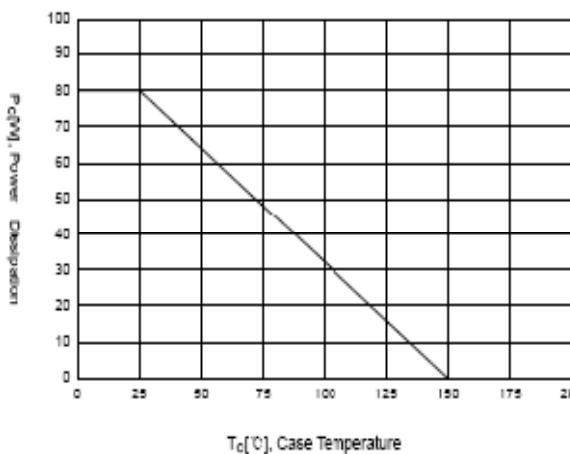


Fig. 3 Power Derating

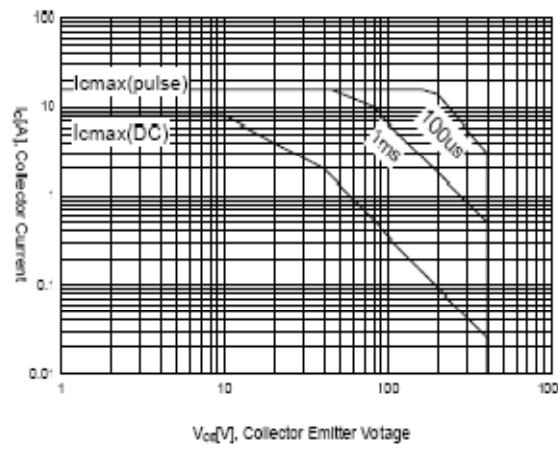


Fig. 4 Safe Operation Area

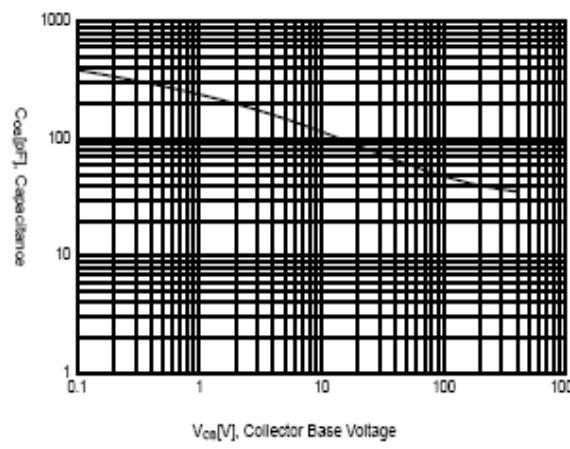


Fig. 5 Collect output capacitance

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## TO-220 Package Dimension

Unit: mm

